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I-68/4e3

474

IEEE TRANSACTIONS ON ELECTRON DEVICES

A PUBLICATION OF THE IEEE ELECTRON DEVICES SOCIETY



MARCH 2013

VOLUME 60

NUMBER 3

IETDAI

(ISSN 0018-9383)

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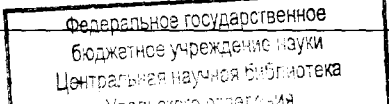
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